

L Number	Hits	S arch T xt	DB	Tim stamp
1	922	438/624.ccls.	USPAT	2003/06/20 12:24
2	1051	438/758,763.ccls.	USPAT	2003/06/20 12:24
3	791	438/778,782.ccls.	USPAT	2003/06/20 12:25
4	654	438/787,784.ccls.	USPAT	2003/06/20 12:25
5	435	438/788,792.ccls.	USPAT	2003/06/20 12:25
6	607	427/573,579.ccls.	USPAT	2003/06/20 12:28
7	1654	118/715.ccls.	USPAT	2003/06/20 12:26
11	7	kilgore-michael\$.in.	EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:27
12	5	kilgore-michael\$.in.	USPAT	2003/06/20 12:28
13	1	kilgore-michael\$.in.	US-PGPUB	2003/06/20 12:28
14	43318	plasma and (chamber react\$6) and cool\$3	USPAT	2003/06/20 12:33
15	8904	(plasma and (chamber react\$6) and cool\$3) and ((wafer substrate) same cool\$3)	USPAT	2003/06/20 12:30
16	2286	((plasma and (chamber react\$6) and cool\$3) and ((wafer substrate) same cool\$3)) and ((wafer substrate) adj2 cool\$3)	USPAT	2003/06/20 12:33
17	1958	((((plasma and (chamber react\$6) and cool\$3) and ((wafer substrate) same cool\$3)) and ((wafer substrate) adj2 cool\$3)) and (plasma same (wafer substrate))	USPAT	2003/06/20 12:31
18	1905	(((((plasma and (chamber react\$6) and cool\$3) and ((wafer substrate) same cool\$3)) and ((wafer substrate) adj2 cool\$3)) and (plasma same (wafer substrate))) and temperature	USPAT	2003/06/20 12:31
19	2995	plasma and (chamber react\$6) and cool\$3	EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:33
20	167	(plasma and (chamber react\$6) and cool\$3) and ((wafer substrate) adj2 cool\$3)	EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:34
21	9595	plasma and (chamber react\$6) and cool\$3	US-PGPUB	2003/06/20 12:33
22	594	(plasma and (chamber react\$6) and cool\$3) and ((wafer substrate) adj2 c l\$3)	US-PGPUB	2003/06/20 12:34